Errata

Publication II: The growth and dissolution rates of iron precipitates in the thin heavily doped boron layer are multiplied by the product of the iron segregation coefficient k_{seg}(B) and the effective diffusion constant of iron D(B) normalized to the bulk diffusion constant.

Publication III: The growth and dissolution rates of iron precipitates in the thin heavily doped boron layer are multiplied by the product of the iron segregation coefficient k_{seg}(B) and the effective diffusion constant of iron D(B) normalized to the bulk diffusion constant.

Publication V: The first processing step in Table 1 should be: Ion implantation mask oxide growth for 50 min at 1050 °C to 435 nm thickness and high temperature annealing for oxygen outdiffusion for 310 min at 1100 °C

The sixth processing step in Table 1 should be: Oxidation for 180 min at 1000 °C and high temperature annealing for phosphorus drive-in and oxide precipitate growth for 1080 min at 1100 °C

The ninth processing step in Table 1 should be: Field oxide growth for 70 min at 1000 °C to 380 nm thickness